



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

17/c
3-18-03
J. Antin

In re the Application of: **TAKEMORI, Toshiyuki et al.**

Group Art Unit: 2814

Serial No.: 09/660,439

Examiner: **Shrinivas (Steven) H. RAO**

Filed: September 12, 2000

P.T.O. Confirmation No.: 6603

For: **TRANSISTOR AND METHOD OF MANUFACTURING THE SAME**

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

March 13, 2003

Sir:

This is a Preliminary Amendment filed along with the Request for Continued Examination (RCE) filed March 13, 2003. Please amend the above-identified application as follows:

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IN THE CLAIMS:

Claims 1 and 11 have been amended as follows:

1. (Twice Amended) A transistor comprising:
- a semiconductor substrate having a semiconductor layer, a drain layer of a first conductivity type provided on said semiconductor layer and a conductive region of a second conductivity type formed by diffusing an impurity of the second conductivity type from a surface of said drain layer;

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